

# IRF7452PbF

## SMPS MOSFET

HEXFET® Power MOSFET

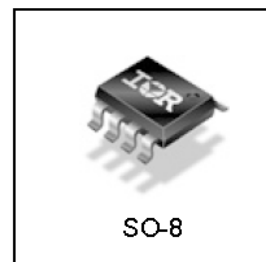
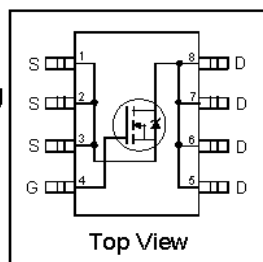
### Applications

- High frequency DC-DC converters
- Lead-Free

$V_{DS}$	$R_{DS(on)}$ max	$I_D$
100V	0.060 $\Omega$	4.5A

### Benefits

- Low Gate to Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective  $C_{OSS}$  to Simplify Design. (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



### Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D$ @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	4.5	A
$I_D$ @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	3.6	
$I_{DM}$	Pulsed Drain Current ①	36	
$P_D$ @ $T_A = 25^\circ\text{C}$	Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/ $^\circ\text{C}$
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$dv/dt$	Peak Diode Recovery $dv/dt$ ③	3.5	V/ns
$T_J$	Operating Junction and	-55 to +150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

### Typical SMPS Topologies

- Telecom 48V input DC-DC with Half Bridge Primary or Datacom 28V input with Passive Reset Forward Converter Primary

Notes ① through ⑤ are on page 8

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## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$ ⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.060	$\Omega$	$V_{GS} = 10V, I_D = 2.7A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 24V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -24V$

## Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	3.4	—	—	S	$V_{DS} = 50V, I_D = 2.7A$
$Q_g$	Total Gate Charge	—	33	50	nC	$I_D = 2.7A$
$Q_{gs}$	Gate-to-Source Charge	—	7.3	11		$V_{DS} = 80V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	16	24		$V_{GS} = 10V, \text{ ④}$
$t_{d(on)}$	Turn-On Delay Time	—	9.5	—	ns	$V_{DD} = 50V$
$t_r$	Rise Time	—	11	—		$I_D = 2.7A$
$t_{d(off)}$	Turn-Off Delay Time	—	16	—		$R_G = 6.0\Omega$
$t_f$	Fall Time	—	13	—		$V_{GS} = 10V, \text{ ④}$
$C_{iss}$	Input Capacitance	—	930	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	300	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	84	—		$f = 1.0MHz$
$C_{oss}$	Output Capacitance	—	1370	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
$C_{oss}$	Output Capacitance	—	170	—		$V_{GS} = 0V, V_{DS} = 80V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	280	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V \text{ ⑤}$

## Avalanche Characteristics

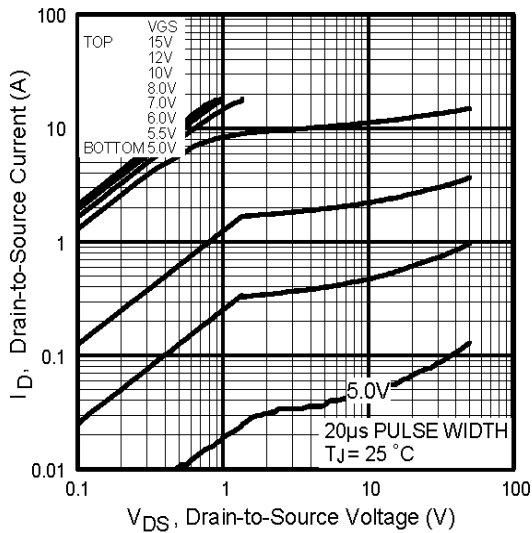
	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	200	mJ
$I_{AR}$	Avalanche Current①	—	4.5	A
$E_{AR}$	Repetitive Avalanche Energy①	—	0.25	mJ

## Thermal Resistance

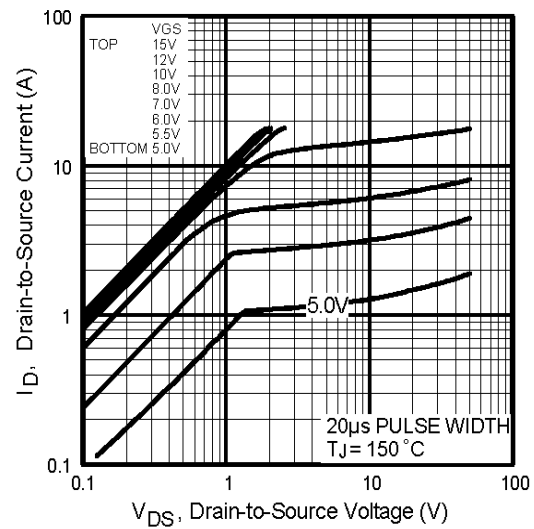
	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient⑥	—	50	°C/W

## Diode Characteristics

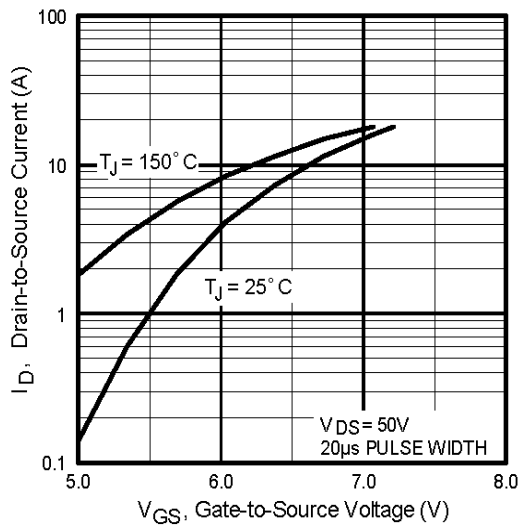
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	36		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 2.7A, V_{GS} = 0V \text{ ④}$
$t_{rr}$	Reverse Recovery Time	—	77	120	ns	$T_J = 25^\circ\text{C}, I_F = 2.7A$
$Q_{rr}$	Reverse Recovery Charge	—	270	410	nC	$di/dt = 100A/\mu s \text{ ④}$



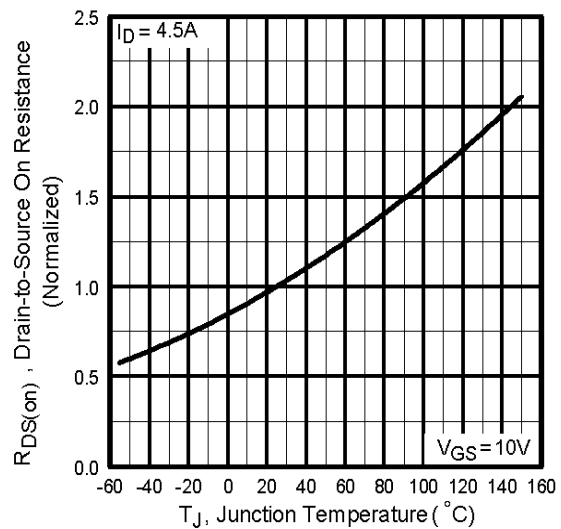
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



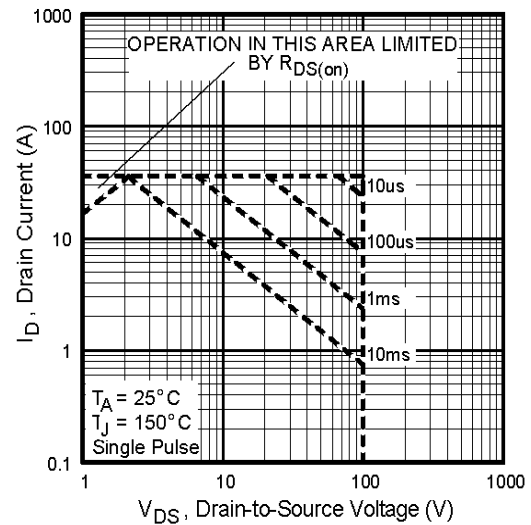
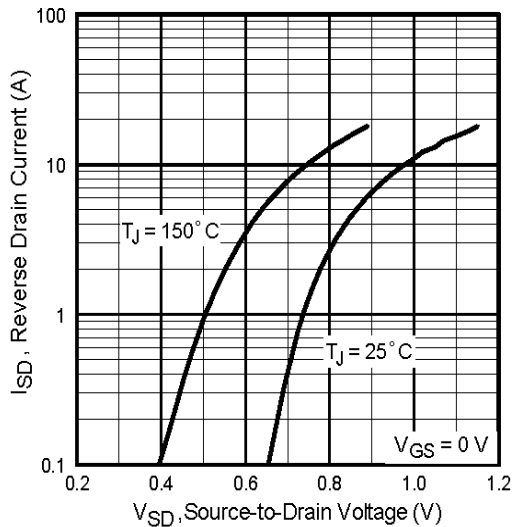
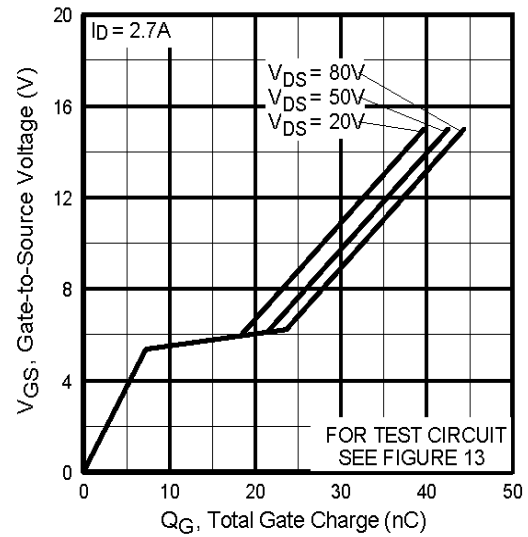
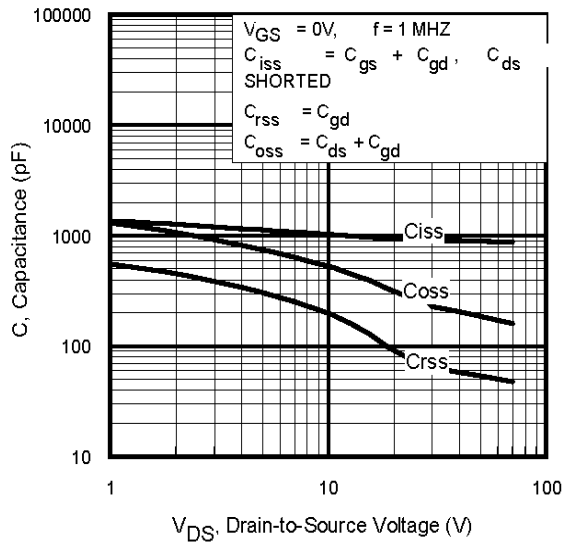
**Fig 3.** Typical Transfer Characteristics

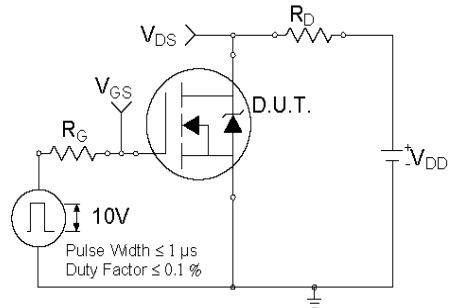
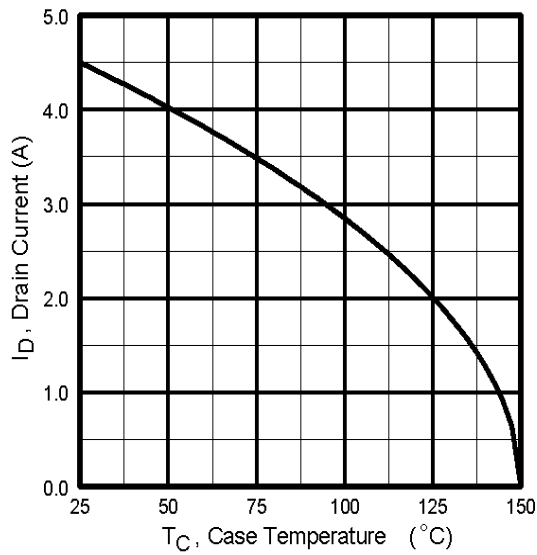


**Fig 4.** Normalized On-Resistance Vs. Temperature

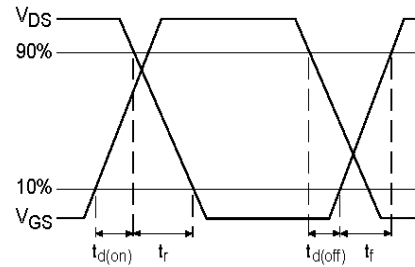
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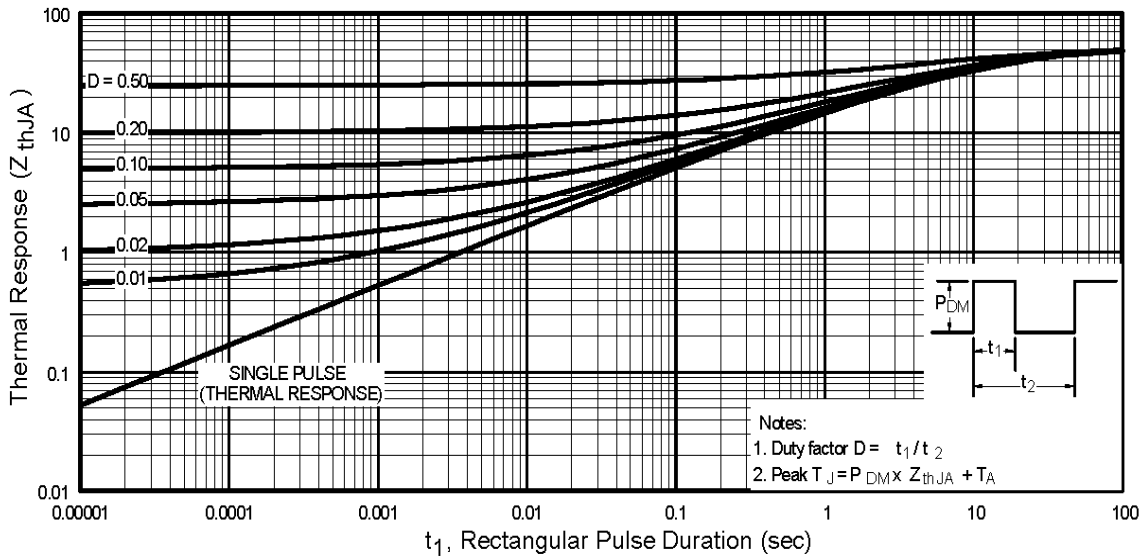




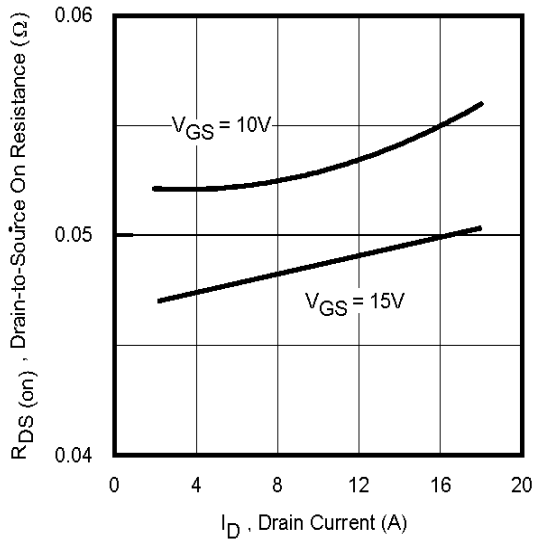
**Fig 10a.** Switching Time Test Circuit



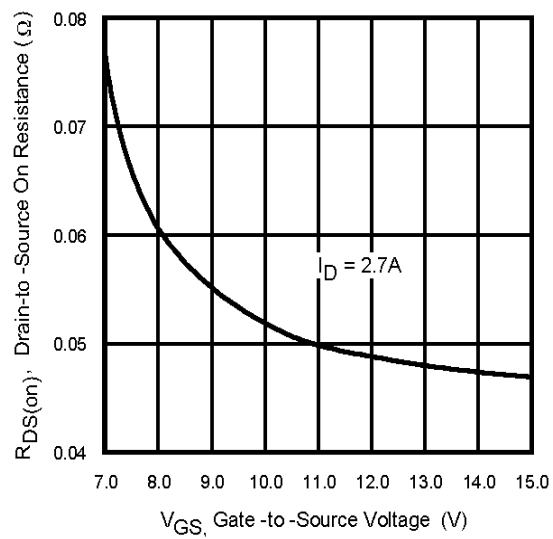
**Fig 10b.** Switching Time Waveforms



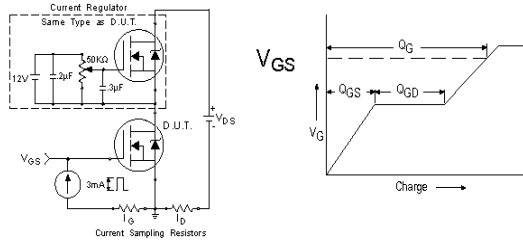
**Fig 10.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient  
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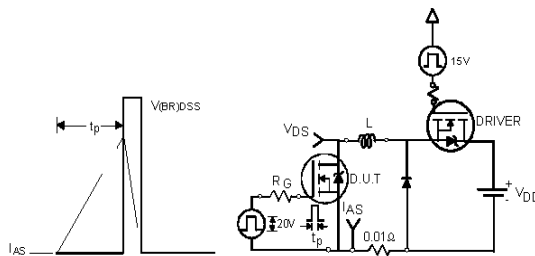
**Fig 12.** On-Resistance Vs. Drain Current



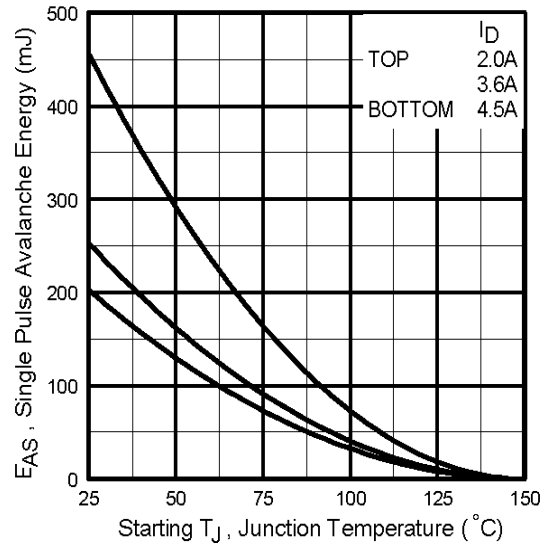
**Fig 13.** On-Resistance Vs. Gate Voltage



**Fig 13a&b.** Basic Gate Charge Test Circuit and Waveform



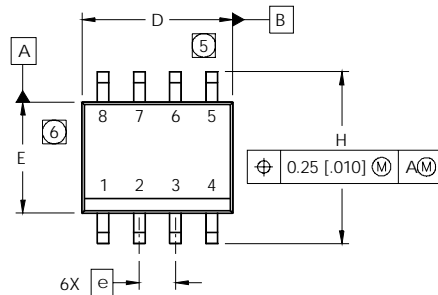
**Fig 14a&b.** Unclamped Inductive Test circuit and Waveforms



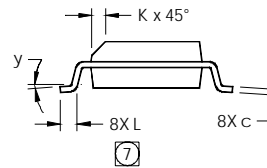
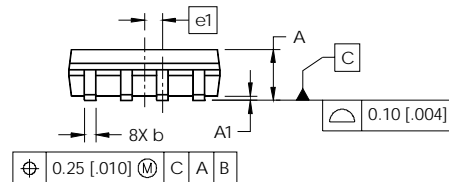
**Fig 14c.** Maximum Avalanche Energy Vs. Drain Current

## SO-8 Package Outline

Dimensions are shown in millimeters (inches)

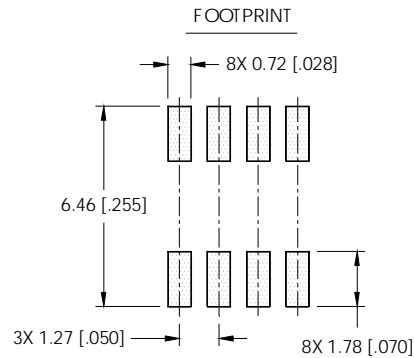


DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



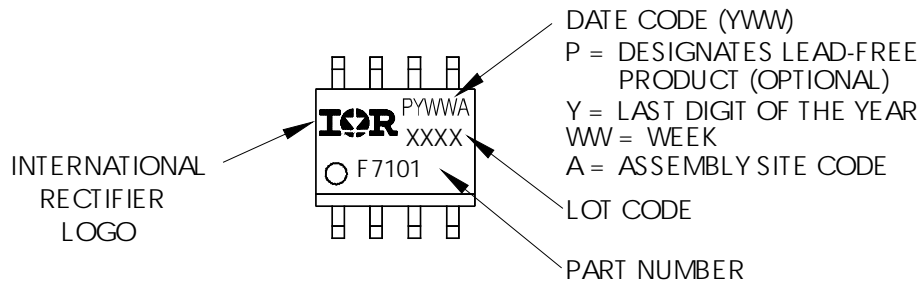
### NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



## SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

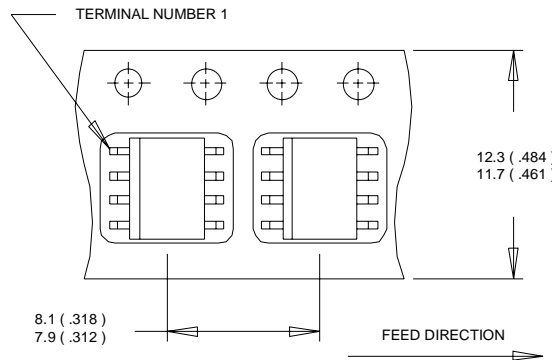


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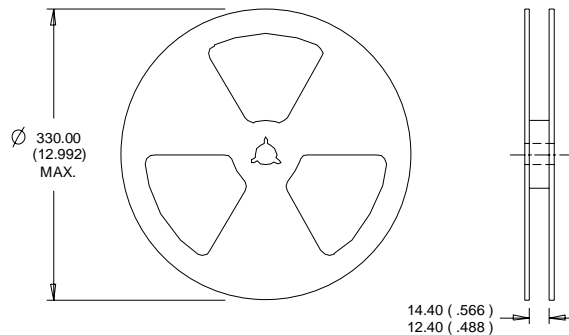
## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



### NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



### NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualifications Standards can be found on IR's Web site.

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